L Number	Hits	Search Text	DB	Time stamp
3	0	20040016963.URPN.	USPAT	2004/03/10 15:57
6	0	20020177285.URPN.	USPAT	2004/03/10 16:05
9	0	20020036319.URPN.	USPAT	2004/03/10 16:08
13	1	6545316.URPN.	USPAT	2004/03/10 16:14
17	2	6174773.URPN.	USPAT	2004/03/10 16:17
19	130	"base region" and "drift region" and trench and ("P/N	USPAT;	2004/03/10 16:26
		junction" or "P-N junction" or "PN junction" or "P N	US-PGPUB;	
		junction")	EPO;	
			DERWENT;	
			IBM TDB	
20	103	(vertical adj MOSFET) and "drift region" and trench	USPĀT;	2004/03/10 16:27
			US-PGPUB;	
			EPO;	
			DERWENT;	
			IBM TDB	
21	87	("base region" and "drift region" and trench and ("P/N	USPAT;	2004/03/10 16:27
	9,	junction" or "P-N junction" or "PN junction" or "P N	US-PGPUB;	200 4,00,10 10.2.
		junction")) not ((vertical adj MOSFET) and "drift region"	EPO;	
		and trench)	DERWENT;	
		and denerty	IBM_TDB	
22	11	(("base region" and "drift region" and trench and ("P/N	USPAT;	2004/03/10 16:28
	• • •	junction" or "P-N junction" or "PN junction" or "P N	US-PGPUB;	200 1/03/10 10.20
		junction")) not ((vertical adj MOSFET) and "drift region"	EPO;	
		and trench)) and "deep trench"	DERWENT;	
		and denerty) and deep dener	IBM TDB	
23	1457	438/197	USPAT;	2004/03/10 17:00
23	1497	430/197	US-PGPUB;	2004/03/10 17.00
			EPO;	
			DERWENT;	
			IBM TDB	
26	0	438/197 and base and drift and trench and P/N	USPAT;	2004/03/10 17:00
20	U	456/177 and base and urite and trenen and 1/10	US-PGPUB;	2004/03/10 17:00
			EPO;	
			DERWENT;	
			IBM TDB	
25	2	438/197 and base and drift and trench and P-N	USPAT;	2004/03/10 17:01
		100/17/ and base and dimeand dentil and 1-14	US-PGPUB;	2007/03/10 17:01
·			EPO;	
			DERWENT;	
			IBM TDB	
27	7	438/197 and base and drift and trench and PN	USPAT;	2004/03/10 17:04
21	<b>'</b> [	150/17/ and base and diffically deficit and 118	US-PGPUB;	2007/03/10 17.07
			EPO;	
			DERWENT;	
			IBM TDB	
28	328	438/212	USPAT;	2004/03/10 17:03
~0	320		US-PGPUB;	2007/03/10 17.03
			EPO;	
			DERWENT;	
			IBM_TDB	
29	, l	438/212 and base and drift and trench and P/N	_	2004/02/10 17:02
		130/412 and base and utill and utillit and I/IV	USPAT;	2004/03/10 17:03
			US-PGPUB;	
			EPO;	
	ļ		DERWENT;	
			IBM_TDB	

31	10	438/212 and base and drift and trench and P-N	USPAT;	2004/03/10 17:05
31	10	456/212 and base and drift and trench and r-in	US-PGPUB;	2004/03/10 17:03
;			EPO;	
			DERWENT;	
			IBM TDB	
32	3	(438/212 and base and drift and trench and P-N) not	USPAT;	2004/03/10 17:04
<b>32</b>		(438/212 and base and drift and trench and P/N) not	US-PGPUB;	200 % 00, 20 27 10 2
		(438/197 and base and drift and trench and PN) not	EPO;	
		(438/197 and base and drift and trench and P-N) not	DERWENT;	
		((("base region" and "drift region" and trench and ("P/N	IBM TDB	
		junction" or "P-N junction" or "PN junction" or "P N		
		junction")) not ((vertical adj MOSFET) and "drift region"		
		and trench)) and "deep trench") not ((vertical adj		
		MOSFET) and "drift region" and trench)		
33	894	438/268	USPAT;	2004/03/10 17:08
		200,200	US-PGPUB;	
			EPO;	
			DERWENT;	
r			IBM TDB	
34	$  $ $  $ $ $	438/268 and base and drift and trench and P/N	USPAT;	2004/03/10 17:08
			US-PGPUB;	
			EPO;	
			DERWENT;	
			IBM TDB	
35	8	438/212 and base and drift and trench and PN	USPAT;	2004/03/10 17:09
		150/212 and base and diffe and treffen and 114	US-PGPUB;	200 405/10 17.07
			EPO;	
			DERWENT;	
			IBM TDB	
36	3	(438/212 and base and drift and trench and PN) not	USPAT;	2004/03/10 17:05
		(438/212 and base and drift and trench and P-N) not	US-PGPUB;	
		(438/212 and base and drift and trench and P/N) not	EPO;	
		(438/197 and base and drift and trench and PN) not	DERWENT;	
		(438/197 and base and drift and trench and P-N) not	IBM TDB	
		((("base region" and "drift region" and trench and ("P/N	_	
		junction" or "P-N junction" or "PN junction" or "PN		
		junction")) not ((vertical adj MOSFET) and "drift region"		
1		and trench)) and "deep trench") not ((vertical adj		
		MOSFET) and "drift region" and trench)		
37	18	438/268 and base and drift and trench and P-N	USPAT;	2004/03/10 17:09
			US-PGPUB;	
			EPO;	
			DERWENT;	
			IBM_TDB	
38	9	(438/268 and base and drift and trench and P-N) not	USPĀT;	2004/03/10 17:07
		(438/212 and base and drift and trench and PN) not	US-PGPUB;	
		(438/212 and base and drift and trench and P-N) not	EPO;	
		(438/212 and base and drift and trench and P/N) not	DERWENT;	
		(438/197 and base and drift and trench and PN) not	IBM_TDB	
		(438/197 and base and drift and trench and P-N) not		
		((("base region" and "drift region" and trench and ("P/N		
		junction" or "P-N junction" or "PN junction" or "P N		
		junction")) not ((vertical adj MOSFET) and "drift region"		
		and trench)) and "deep trench") not ((vertical adj		·
		MOSFET) and "drift region" and trench)		
39	27	438/268 and base and drift and trench and PN	USPAT;	2004/03/10 17:07
			US-PGPUB;	
			EPO;	
			DERWENT;	
<u> </u>	<u></u>		IBM_TDB	

40	15	(438/268 and base and drift and trench and PN) not	USPAT;	2004/03/10 17:09
40	15	(438/268 and base and drift and trench and P-N) not	US-PGPUB;	2004/03/10 17.09
		(438/212 and base and drift and trench and PN) not	EPO;	
		(438/212 and base and drift and trench and P-N) not	DERWENT;	
	1	(438/212 and base and drift and trench and P/N) not	IBM TDB	
		(438/197 and base and drift and trench and PN) not	IBW_IBB	
		(438/197 and base and drift and trench and P-N) not		
		((("base region" and "drift region" and trench and ("P/N		
		junction" or "P-N junction" or "PN junction" or "P N		
		junction")) not ((vertical adj MOSFET) and "drift region"	]	
		and trench)) and "deep trench") not ((vertical adj		
		MOSFET) and "drift region" and trench)		
41	1043	438/270	USPAT;	2004/03/10 17:08
			US-PGPUB;	
			EPO;	
			DERWENT;	
			IBM TDB	
42	2	438/270 and base and drift and trench and P/N	USPĀT;	2004/03/10 17:08
	1.		US-PGPUB;	
			EPO;	
			DERWENT;	
			IBM_TDB	
43	21	438/270 and base and drift and trench and PN	USPAT;	2004/03/10 17:09
			US-PGPUB;	
			EPO;	
			DERWENT;	
			IBM_TDB	
44	20	438/270 and base and drift and trench and P-N	USPAT;	2004/03/10 17:09
			US-PGPUB;	
			EPO;	
			DERWENT;	
4.5	_	/ 40 0 /0 70	IBM_TDB	0004/00/10 17 10
45	5	(438/270 and base and drift and trench and PN) not	USPAT;	2004/03/10 17:10
		(438/268 and base and drift and trench and PN) not	US-PGPUB;	
		(438/268 and base and drift and trench and P-N) not	EPO;	
		(438/212 and base and drift and trench and PN) not (438/212 and base and drift and trench and P-N) not	DERWENT; IBM TDB	
		(438/212 and base and drift and trench and P/N) not		
		(438/197 and base and drift and trench and PN) not		
		(438/197 and base and drift and trench and P-N) not		
		((("base region" and "drift region" and trench and ("P/N		
	ļ	junction" or "P-N junction" or "PN junction" or "P N		
		junction")) not ((vertical adj MOSFET) and "drift region"		
		and trench)) and "deep trench") not ((vertical adj		
		MOSFET) and "drift region" and trench)		
47	3	(438/270 and base and drift and trench and P-N) not	USPAT;	2004/03/10 17:11
		(438/270 and base and drift and trench and PN) not	US-PGPUB;	, ,
		(438/268 and base and drift and trench and PN) not	EPO;	
		(438/268 and base and drift and trench and P-N) not	DERWENT;	
		(438/212 and base and drift and trench and PN) not	IBM_TDB	
		(438/212 and base and drift and trench and P-N) not	_	
		(438/212 and base and drift and trench and P/N) not		
		(438/197 and base and drift and trench and PN) not		
		(438/197 and base and drift and trench and P-N) not		
		((("base region" and "drift region" and trench and ("P/N		
		junction" or "P-N junction" or "PN junction" or "P N		
•		junction")) not ((vertical adj MOSFET) and "drift region"		
		and trench)) and "deep trench") not ((vertical adj		
		MOSFET) and "drift region" and trench)		

48		(138/270 and base and drift and transh and D/NI) not	LICDAT.	2004/03/10 17:17
70	0	(438/270 and base and drift and trench and P/N) not (438/270 and base and drift and trench and P-N) not	USPAT; US-PGPUB;	200 <del>4</del> /03/10 17:17
		`	· · · · · · · · · · · · · · · · · · ·	
		(438/270 and base and drift and trench and PN) not	EPO;	
		(438/268 and base and drift and trench and PN) not	DERWENT;	
		(438/268 and base and drift and trench and P-N) not	IBM_TDB	
	<u> </u>	(438/212 and base and drift and trench and PN) not		
		(438/212 and base and drift and trench and P-N) not		
		(438/212 and base and drift and trench and P/N) not		
		(438/197 and base and drift and trench and PN) not		
		(438/197 and base and drift and trench and P-N) not		
		((("base region" and "drift region" and trench and ("P/N		
		junction" or "P-N junction" or "PN junction" or "P N		
		junction")) not ((vertical adj MOSFET) and "drift region"		
		and trench)) and "deep trench") not ((vertical adj		
		MOSFET) and "drift region" and trench)		
49	71	UMOSFET and drift and base	USPAT;	2004/03/10 17:11
			US-PGPUB:	
			EPO;	
			DERWENT;	
			IBM TDB	
50	36	(UMOSFET and drift and base ) not (438/270 and base	USPAT;	2004/03/10 17:15
30	30	and drift and trench and P-N) not (438/270 and base	US-PGPUB;	2004/03/10 17.13
	ļ			
		and drift and trench and PN) not (438/268 and base and	EPO;	
		drift and trench and PN) not (438/268 and base and	DERWENT;	
	}	drift and trench and P-N) not (438/212 and base and	IBM_TDB	
		drift and trench and PN) not (438/212 and base and		
		drift and trench and P-N) not (438/212 and base and		
		drift and trench and P/N) not (438/197 and base and		
		drift and trench and PN) not (438/197 and base and		
		drift and trench and P-N) not ((("base region" and "drift		
		region" and trench and ("P/N junction" or "P-N junction"		
		or "PN junction" or "P N junction")) not ((vertical adj		
		MOSFET) and "drift region" and trench)) and "deep		
		trench") not ((vertical adj MOSFET) and "drift region"		
		and trench)		
51	353	power and MOSFET and drift and (surface adj4	USPAT;	2004/03/10 17:17
		electrode)	US-PGPUB;	
		,	EPO; IPO;	
			DERWENT;	
			IBM TDB	
52	211	(power and MOSFET and drift and (surface adj4	USPAT;	2004/03/10 17:17
J_		electrode)) and trench	US-PGPUB;	2007/03/10 17.17
		ciccioacj, and achen	EPO; JPO;	
			· ·	
			DERWENT;	
52	120	//nower and MOCEET and different / Control	IBM_TDB	0004/00/10 17 17
53	139	((power and MOSFET and drift and (surface adj4	USPAT;	2004/03/10 17:17
		electrode)) and trench) and (PN or P/N or P-N)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

			<del></del>	<del></del>
54	71	(((power and MOSFET and drift and (surface adj4	USPAT;	2004/03/10 17:23
		electrode)) and trench) and (PN or P/N or P-N)) not	US-PGPUB;	
		(438/270 and base and drift and trench and P/N) not	EPO;	
		(438/270 and base and drift and trench and P-N) not	DERWENT;	
		(438/270 and base and drift and trench and PN) not	IBM_TDB	
		(438/268 and base and drift and trench and PN) not		
		(438/268 and base and drift and trench and P-N) not		
		(438/212 and base and drift and trench and PN) not		
		(438/212 and base and drift and trench and P-N) not		
		(438/212 and base and drift and trench and P/N) not		
}		(438/197 and base and drift and trench and PN) not		
		(438/197 and base and drift and trench and P-N) not		
		((("base region" and "drift region" and trench and ("P/N		
		junction" or "P-N junction" or "PN junction" or "P N		
		junction")) not ((vertical adj MOSFET) and "drift region"		
		,		
		and trench)) and "deep trench") not ((vertical adj		
	0.5	MOSFET) and "drift region" and trench)	I ICD AT	0004/00/10 17 10
55	25	((((power and MOSFET and drift and (surface adj4	USPAT;	2004/03/10 17:18
		electrode)) and trench) and (PN or P/N or P-N)) not	US-PGPUB;	
		(438/270 and base and drift and trench and P/N) not	EPO;	
		(438/270 and base and drift and trench and P-N) not	DERWENT;	
		(438/270 and base and drift and trench and PN) not	IBM_TDB	
		(438/268 and base and drift and trench and PN) not		
		(438/268 and base and drift and trench and P-N) not		
		(438/212 and base and drift and trench and PN) not		
		(438/212 and base and drift and trench and P-N) not		
		(438/212 and base and drift and trench and P/N) not		
		(438/197 and base and drift and trench and PN) not		
		(438/197 and base and drift and trench and P-N) not		
		((("base region" and "drift region" and trench and ("P/N		
		junction" or "P-N junction" or "PN junction" or "P N		
		junction")) not ((vertical adj MOSFET) and "drift region"		
		and trench)) and "deep trench") not ((vertical adj		
		MOSFET) and "drift region" and trench)) and deep		
56	80	"vertical MOSFET" and drift and (PN or P/N or P-N) and	USPAT;	2004/03/10 17:23
] 30	80	,	ĺ	2004/03/10 17:23
		base and trench	US-PGPUB;	
			EPO;	
			DERWENT;	
<i></i>		/# . 13.400 CIPTOCIN 13.40 1/554 554 554	IBM_TDB	0004/00/10 17 00
57	6	("vertical MOSFET" and drift and (PN or P/N or P-N)	USPAT;	2004/03/10 17:23
		and base and trench) not (((power and MOSFET and	US-PGPUB;	
		drift and (surface adj4 electrode)) and trench) and (PN	EPO;	
		or P/N or P-N)) not (438/270 and base and drift and	DERWENT;	
		trench and P/N) not (438/270 and base and drift and	IBM_TDB	
		trench and P-N) not (438/270 and base and drift and		
		trench and PN) not (438/268 and base and drift and		
		trench and PN) not (438/268 and base and drift and		
		trench and P-N) not (438/212 and base and drift and		
		trench and PN) not (438/212 and base and drift and		
		trench and P-N) not (438/212 and base and drift and		
		trench and P/N) not (438/197 and base and drift and		
		trench and PN) not (438/197 and base and drift and		
		trench and P-N) not ((("base region" and "drift region"		
		and trench and ("P/N junction" or "P-N junction" or "PN		
		junction" or "P N junction")) not ((vertical adj MOSFET)		
		and "drift region" and trench)) and "deep trench") not		
		((vertical adj MOSFET) and "drift region" and trench)		
L	<u></u>	((vertical au) (vicor Di) and diffe (egion and deficit)	<u> </u>	<u> </u>

r <del></del>			T-1-12-1-1	
-	2	5912497.pn.	USPAT;	2004/03/08 11:06
			US-PGPUB;	
			EPO;	
			DERWENT;	
			IBM_TDB	
-	103	(vertical adj MOSFET) and "drift region" and trench	USPAT;	2004/03/10 16:27
			US-PGPUB;	
		· ·	EPO;	
			DERWENT;	
			IBM_TDB	
-	2	6388286.pn.	USPAT;	2004/03/08 15:23
			US-PGPUB;	
			EPO;	
			DERWENT;	
			IBM TDB	
-	3	6452230.pn.	USPAT;	2004/03/08 15:21
			US-PGPUB;	
			EPO;	
			DERWENT;	
			IBM TDB	
	2	5756386.pn.	USPAT;	2004/03/08 15:23
	2	7.30300.pm	US-PGPUB;	200 400,00 10.20
			EPO;	
			DERWENT;	
			IBM TDB	
	2	5062902 nn	USPAT;	2004/02/09 15:22
-	2	5962893.pn.	1	2004/03/08 15:22
			US-PGPUB;	
			EPO;	
1			DERWENT;	
	2	<0.01100 mg	IBM_TDB	2004/02/00 15 04
-	2	6091108.pn.	USPAT;	2004/03/08 15:24
			US-PGPUB;	
			EPO;	
			DERWENT;	
		E127570	IBM_TDB	0004/00/00 15 05
-	2	5177572.pn.	USPAT;	2004/03/08 15:25
		•	US-PGPUB;	
	-		EPO;	
			DERWENT;	
	_	5001000	IBM_TDB	0004/00/00 15 01
-	2	5831288.pn.	USPAT;	2004/03/08 15:26
			US-PGPUB;	
			EPO;	
			DERWENT;	
		5410041	IBM_TDB	0004/00/00 15 01
-	2	5412241.pn.	USPAT;	2004/03/08 15:26
			US-PGPUB;	
			EPO;	
			DERWENT;	
		, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	
-	103	(vertical adj MOSFET) and "drift region" and trench	USPAT;	2004/03/10 16:23
			US-PGPUB;	
			EPO;	
			DERWENT;	
		<u>                                     </u>	IBM_TDB	